Docket No.: 64965-168 **PATENT**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of	:	
QI XIANG	:	
Serial No.: Divisional of Application No. 10/015,808	:	Group Art Unit: To be assigned
Filed: July 17, 2003	:	Examiner: To be assigned

For: CMOS WITH STRAINED SILICON CHANNEL NMOS AND SILICON GERMANIUM CHANNEL PMOS

INFORMATION DISCLOSURE STATEMENT

Mail Stop NEW APPLICATIONS
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached form PTO-1449. It is respectfully requested that the references be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

The references were cited by or submitted to the U.S. Patent and Trademark Office in parent application Serial No. 10/015,808 , filed December 17, 2001 , which is relied upon for an

earlier filing date under 35 USC 120. Thus, copies of these references are not attached. 37 CFR 1.98(d).

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

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Date: July 17, 2003

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(PTO-1449)

ATTY. DOCKET NO.	SERIAL NO.
64965-168	**Divisional of Serial No. 10/015,808**
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FILING DATE: **July 17, 2003**	GROUP: **To be assigned**

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code2 (if known)		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
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		Hitachi America, Ltd., Semiconductor Equipment Group, "Customizable Shallow Trench Isolation, "http://www.hitachi.com/semiequipment/sti.html/>pg 1
		SNP Applications/Shallow Trench Isolation (STI), "Shallow Trench Isolation (STD)," http://www.surfaceinterface.com/snpappsSTI.html/>, pgs 1-2
		Institute of Microelectronics - Deep Submicron - Shallow Trench Isolation, "Shallow Trench Isolation Module Developmetn", http://www.ime.org.sg/deep_trench.htm/>, pgs. 1-2

EXAMINER	DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

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		US			
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		US			
		US			
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		US			

FOREIGN PATENT DOCUMENTS

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						Yes	No

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
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		Orla Higgins, Press Release, "Amber Wave Systems Corporation Announces Availability of Breakthrough Strained Silicon Technology", October 22, 2001, pgs. 1-4	
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